



Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Isolated plastic package
- Low leakage current •
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC) •
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Dynamic characteristics	Pa	Parameter	Conditions	Values				Unit
$\begin{tabular}{ c c c c c } \hline voltage & & & & & & & & & & & & & & & & & & &$	na	aximum rating						
$\begin{array}{ c c c c } \hline Fig. 1; Fig. 2; Fig. 3 \\ \hline \delta = 0.5; t_p = 25 \ \mu s; T_h \le 51 \ ^\circ C; \\ square-wave pulse \\ \hline \delta = 0.5; t_p = 25 \ \mu s; T_h \le 51 \ ^\circ C; \\ square-wave pulse \\ \hline I_{FSM} \\ \hline non-repetitive peak \\ forward current \\ \hline t_p = 10 \ ms; T_{j(nit)} = 25 \ ^\circ C; sine-wave pulse; \\ \hline Fig. 4 \\ \hline t_p = 8.3 \ ms; T_{j(nit)} = 25 \ ^\circ C; sine-wave pulse \\ \hline 200 \\ \hline Symbol \\ \hline Parameter \\ \hline Conditions \\ \hline Min \\ \hline Typ \\ \hline Static characteristics \\ \hline V_F \\ \hline forward voltage \\ \hline I_F = 30 \ A; \ T_j = 25 \ ^\circ C; \ Fig. 6 \\ \hline I_F = 30 \ A; \ T_j = 150 \ ^\circ C; \ Fig. 6 \\ \hline I_F = 30 \ A; \ Fig. 1 \ A; \ Fig. $					6	00		V
$\begin{tabular}{ c c c c c } \hline current & square-wave pulse & $$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	a١	average forward current		30			A	
$\begin{tabular}{ c c c c c c } \hline Fig. 4 & & & & & & & & & & & & & & & & & & $				60			A	
SymbolParameterConditionsMinTypStatic characteristics V_F forward voltage $I_F = 30 \text{ A}; T_j = 25 \text{ °C}; Fig. 6$ -2 $I_F = 30 \text{ A}; T_j = 150 \text{ °C}; Fig. 6$ -1.38Dynamic characteristics				200		A		
Static characteristics V_F forward voltage I_F = 30 A; T_j = 25 °C; Fig. 6 - 2 $I_F = 30 A; T_j = 150 °C; Fig. 6$ - 1.38 Dynamic characteristics			t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		2	20		А
V _F forward voltage I _F = 30 A; T _j = 25 °C; Fig. 6 - 2 I _F = 30 A; T _j = 150 °C; Fig. 6 - 1.38 Dynamic characteristics - 1.38	P	Parameter	Conditions		Min	Тур	Max	Unit
$I_{F} = 30 \text{ A}; T_{j} = 150 \text{ °C}; Fig. 6$ Dynamic characteristics	ra	acteristics						
Dynamic characteristics	fo	orward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2	2.75	V
			I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.8	V
t_{rr} reverse recovery time $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/µs};$	h	naracteristics	•		,			
T _i = 25 °C; <u>Fig. 7</u>	e،	everse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 50 A/μs; T _i = 25 °C; <u>Fig. 7</u>		-	-	35	ns

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	
2	A	anode		К — Ң — А
mb	n.c.	mounting base; isolated	SOD113 (2-lead TO-220F)	001aaa020

6. Ordering information

Table 3. Ordering inform	nation		
Type number	Package		
	Name	Description	Version
BYC30X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

7. Marking

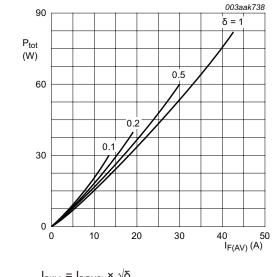
Table 4. Marking codes								
Type number	Marking codes							
BYC30X-600P	BYC30X-600P							

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V _{RRM}	repetitive peak reverse voltage		600	V
V _{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _h ≤ 51 °C; Fig. 1; Fig. 2; Fig. 3	30	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _h ≤ 51 °C; square-wave pulse	60	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.798 \text{ V; } \text{R}_{\text{s}} = 0.003 \ \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

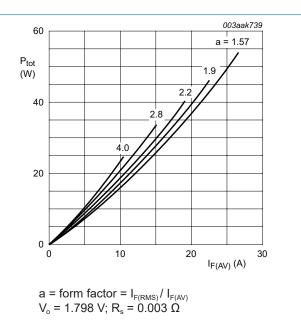
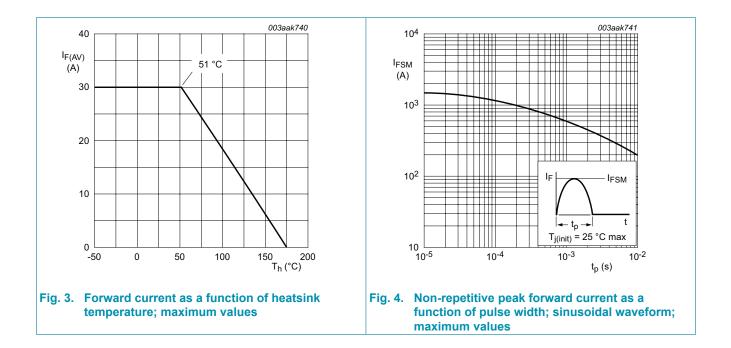


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

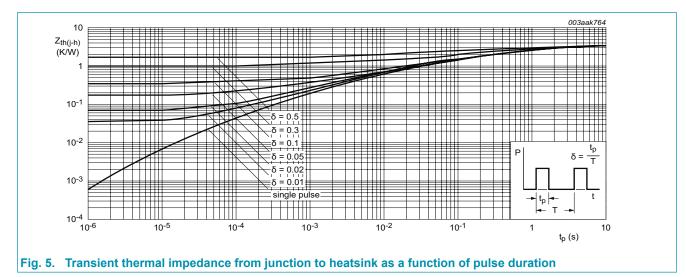
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BYC30X-600P Ultrafast power diode



9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-h)}}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	3.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



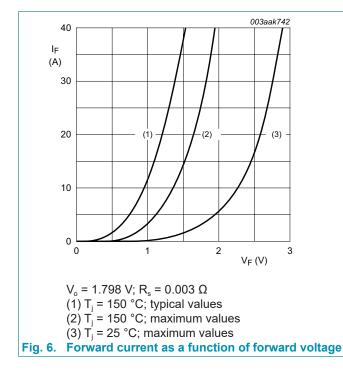
10. Isolation characteristics

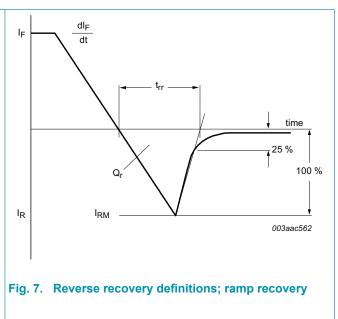
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	PF

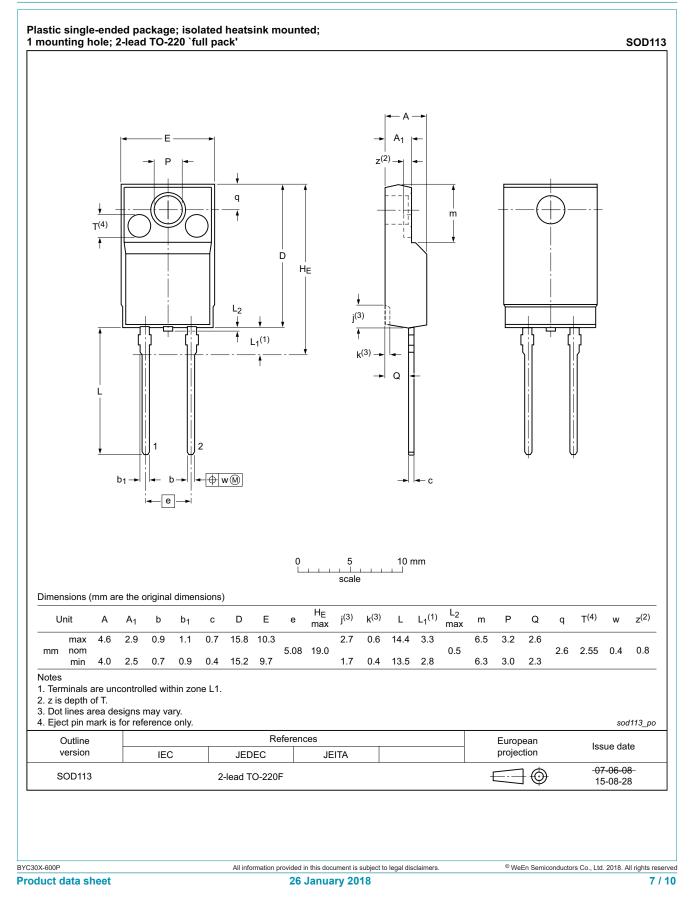
11. Characteristics

Table 8. C	haracteristics					
Symbol	Parameter	er Conditions			Max	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	600	μA
Dynamic	characteristics		I			_
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	-	35	ns
		$ \begin{array}{l} I_{F} = 30 \text{ A}; V_{R} = 200 \text{ V}; dI_{F}/\text{dt} = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 25 \ ^{\circ}\text{C}; \ \overline{\text{Fig. } 7} \end{array} $	-	-	35	ns
		$I_{F} = 30 \text{ A}; V_{R} = 200 \text{ V}; dI_{F}/dt = 200 \text{ A}/\mu\text{s}; T_{j} = 125 \text{ °C}; Fig. 7$	-	70	-	ns
I _{RM}	peak reverse recovery current	$I_{F} = 30 \text{ A}; V_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; T_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	3.5	-	A
		$I_{F} = 30 \text{ A}; V_{R} = 200 \text{ V}; dI_{F}/dt = 200 \text{ A}/\mu\text{s}; T_{j} = 125 \text{ °C}; Fig. 7$	-	7.6	-	A
Q _r	recovered charge	$ \begin{array}{l} {\sf I}_{\sf F} = 30 \; {\sf A}; \; {\sf V}_{\sf R} = 200 \; {\sf V}; \; {\sf dI}_{\sf F}/{\sf dt} = 200 \; {\sf A}/\mu {\sf s}; \\ {\sf T}_{\sf j} = 25 \; {}^{\circ}{\sf C}; \; \underline{{\sf Fig. 7}} \end{array} $	-	50	-	nC
		$I_{F} = 30 \text{ A}; V_{R} = 200 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; T_{j} = 125 \text{ °C}; Fig. 7$	-	280	-	nC





12. Package outline



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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14. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Isolation characteristics	5
11. Characteristics	6
12. Package outline	7
13. Legal information	8
14. Contents	10

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